

# ABSTRACT

Disclosed is a bit line-manufacturing method, by which  
a bit line having a fine width can be easily manufactured.

The method comprises the steps of: successively forming a

- 5 conducting layer and an insulating layer on a substrate, the  
conducting layer serving to form a bit line; forming a first  
mask pattern on the insulating layer in such a manner that a  
desired region of the insulating layer is exposed; etching  
the first mask pattern, so as to form a second mask pattern;  
10 removing the insulating layer using the second mask pattern;  
removing the second mask pattern; and removing the  
conducting layer using the remaining insulating layer as a  
mask, so as to form the bit line.